

20V 6A N-Channel Enhancement Mode Power MOSFET

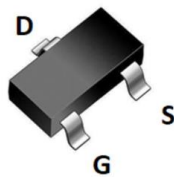
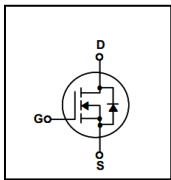
General Description

This Power MOSFET has been developed using advanced trench process, which is specifically designed to minimize input capacitance and gate charge. This renders the device suitable for use as primary switch in advanced high-efficiency isolated DC-DC converters for telecom and computer applications, and applications with low gate charge driving requirements.

FEATURES

- $R_{DS(ON)} \leq 33m\Omega$ @ $V_{GS}=4.5V, I_D=5A$
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead free product is acquired

SYMBOL



SOT-23 top view

ASSEMBLY MESSAGE

Product Name	Marking	Package	Packaging
BXT330N02M	3420 X	SOT-23	Reel

ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Rating	Unit
			SOT-23	
Drain-Source Voltage		V_{DSS}	20	V
Drain Current	Continuous ($T_C = 25^\circ\text{C}$)	I_D	6	A
	Continuous ($T_C = 100^\circ\text{C}$)		4.8	A
Drain Current	Pulsed (Note1)	I_{DM}	24	A
Gate-Source Voltage		V_{GSS}	± 10	V
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	1.25	W
Maximum Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 to 150	$^\circ\text{C}$

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

THERMAL CHARACTERISTICS

Parameter	Symbol	Max.	Unit
		SOT-23	
Thermal Resistance, Junction-to- Ambient	R _{θJA}	100	°C / W

ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V, ID=250μA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	VDS=20V, VGS=0V			1	μA
Gate-Body Leakage Current, Forward	I _{GSS}	VGS=10V			100	nA
Gate-Body Leakage Current, Reverse		VGS=-10V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	VGS(TH)	VDS=VGS, ID=250μA	0.5	0.65	1.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	VGS=4.5V, ID=5A		21	33	mΩ
		VGS=2.5V, ID=4A		27	40	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	VDS=10V, VGS=0V, f=1.0MHz		525		pF
Output Capacitance	C _{OSS}			94		pF
Reverse Transfer Capacitance	C _{RSS}			73		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	t _{D(ON)}	VDD=10V, ID=6A, VGS = 4.5V, RG=1Ω		4		ns
Turn-ON Rise Time	t _R			8		ns
Turn-OFF Delay Time	t _{D(OFF)}			18		ns
Turn-OFF Fall-Time	t _F			7		ns
Total Gate Charge(Note2)	Q _G	VDS =10V, VGS =4.5V, ID =6A		11		nC
Gate Source Charge	Q _{GS}			1.2		nC
Gate Drain Charge	Q _{GD}			1.9		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	IS=6A, VGS=0V			1.2	V
Diode Continuous Forward Current	I _S				6	A

Note: 2. Essentially independent of operating temperature

TYPICAL CHARACTERISTICS

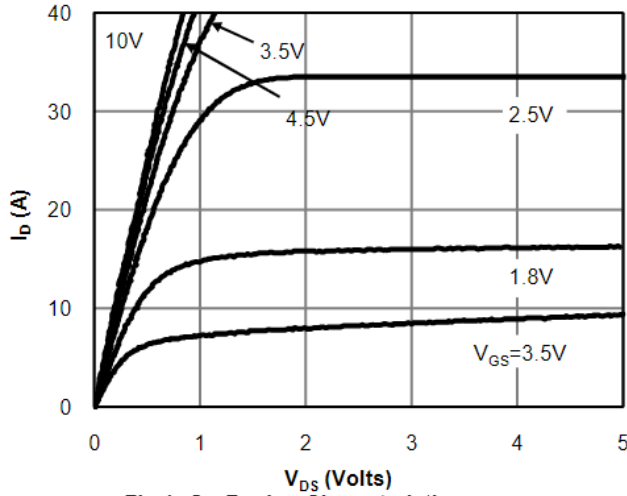


Fig 1: On-Region Characteristics

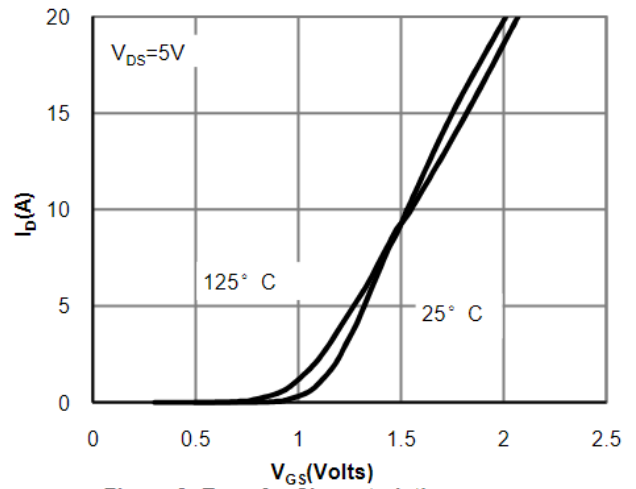


Figure 2: Transfer Characteristics

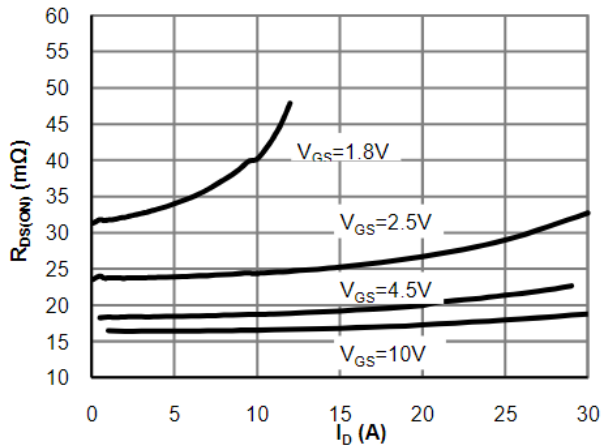


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

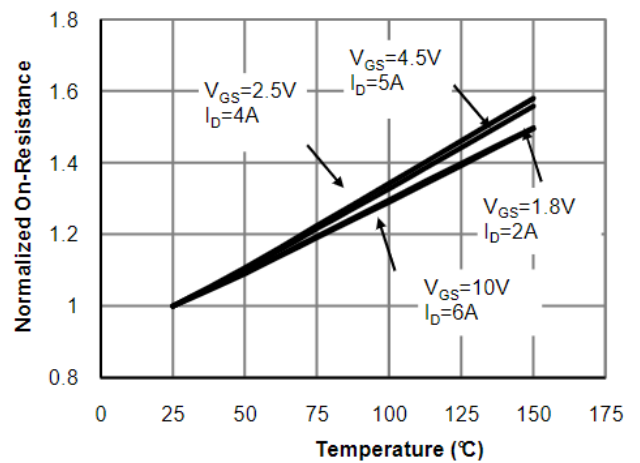


Figure 4: On-Resistance vs. Junction Temperature

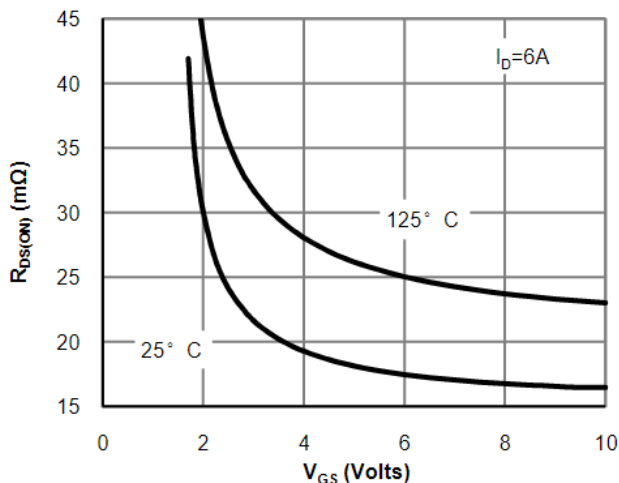


Figure 5: On-Resistance vs. Gate-Source Voltage

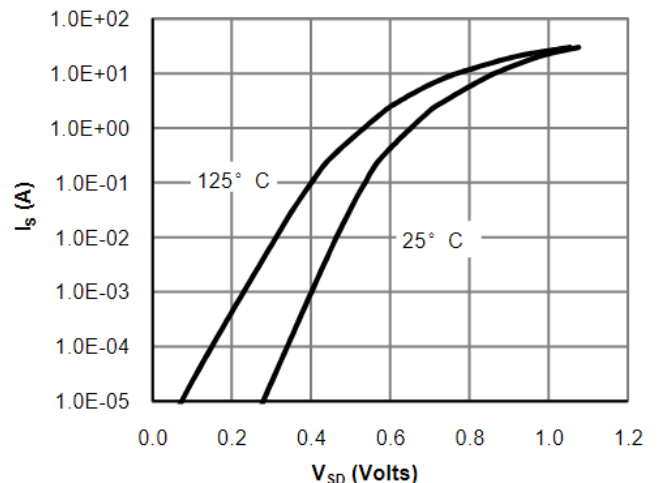


Figure 6: Body-Diode Characteristics

